

ESDLLC5V0D8BH

Features

- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.25pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 20\text{kV}$
 - Contact discharge: $\pm 15\text{kV}$
 - IEC61000-4-5 (Lightning) 4.5A (8/20 μs)
- RoHS Compliant
- Lead Finish: NiPdAu

Description

The ESDLLC5V0D8BH is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ESDLLC5V0D8BH has an ultra-low capacitance with a typical value at 0.25pF, and complies with the IEC 61000-4-2 (ESD) standard with $\pm 15\text{kV}$ air and $\pm 8\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN

Absolute Maximum Ratings

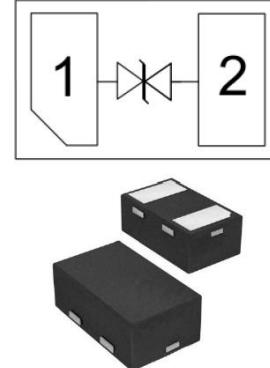
Tamb=25°C unless otherwise specified

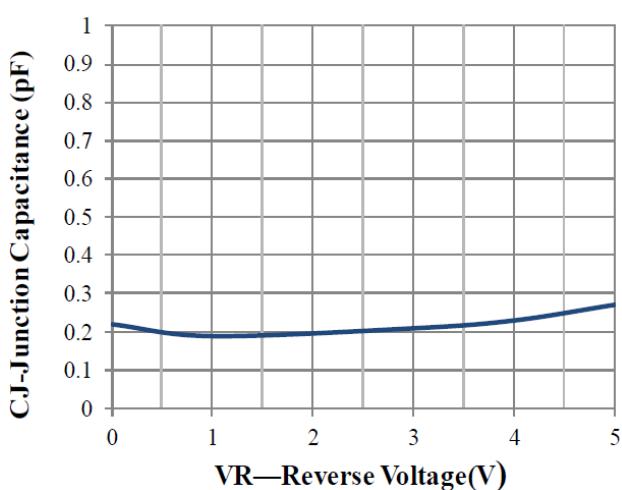
| Parameter | Symbol | Value | Unit |
|--|--------------------------------|-------------|------|
| Peak Pulse Power (8/20 μs) | P _{pp} | 110 | W |
| Maximum Reverse Peak Pulse Current | I _{PP} * ¹ | 4.5 | A |
| ESD per IEC 61000-4-2 (Air) | V _{ESD} | ± 20 | KV |
| ESD per IEC 61000-4-2 (Contact) | | ± 15 | |
| Storage Temperature Range | T _{STJ} | -55 to +150 | °C |
| Operating Temperature Range | T _J | -55 to +125 | °C |

Electrical Characteristics

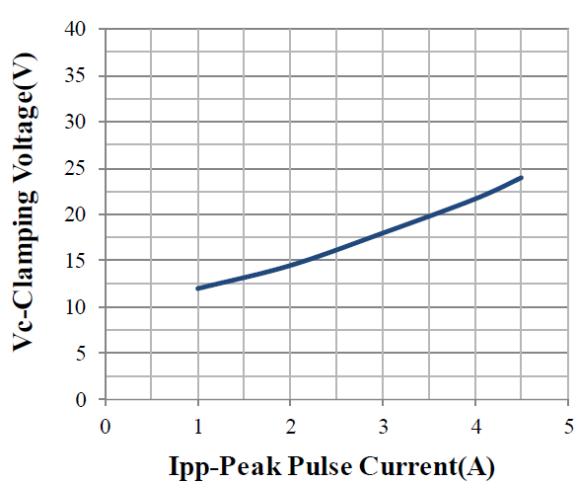
TA=25°C unless otherwise specified

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|------------------|------------------------------|---|-----|------|------|---------------|
| V _{RWM} | Reverse Working Peak Voltage | - | | | 5.0 | V |
| V _{BR} | Reverse Breakdown Voltage | I _T = 1mA | 6.0 | 7.5 | 8.5 | V |
| I _R | Reverse Current | V _{RWM} = 5V | | | 0.5 | μA |
| V _C | Clamping Voltage | I _{PP} =1A, t _P =8/20 μs | | | 12 | V |
| V _C | Clamping Voltage | I _{PP} =4.5A, t _P =8/20 μs | | 18 | 20 | V |
| C _D | Diode Capacitance | V _R = 0V, f = 1MHz | | 0.22 | 0.30 | pF |

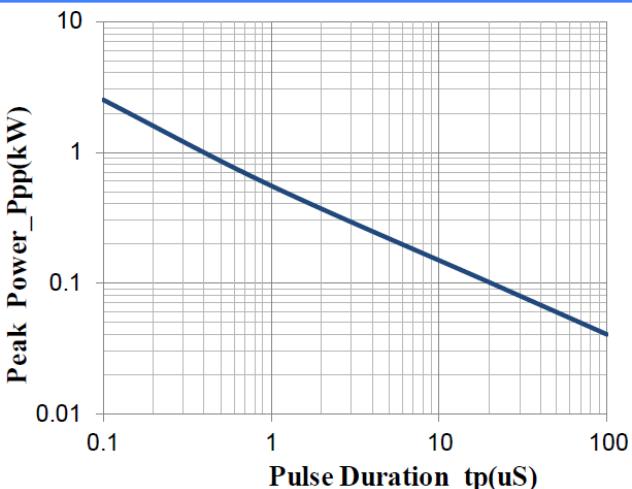


Characteristic Curves


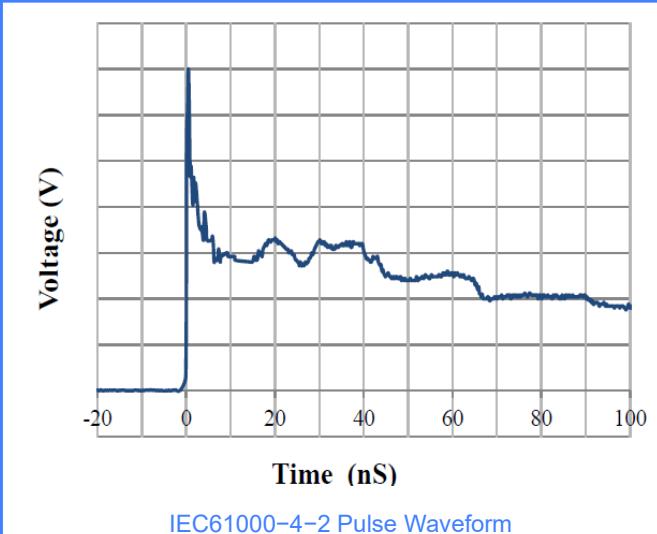
Junction Capacitance vs. Reverse Voltage



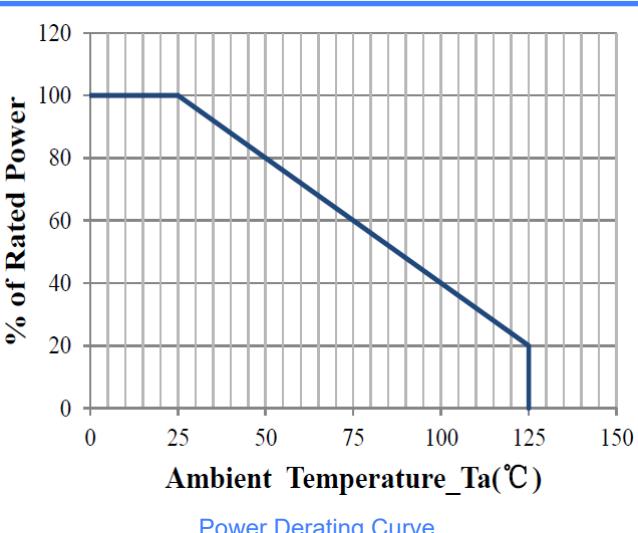
Clamping Voltage vs. Peak Pulse Current



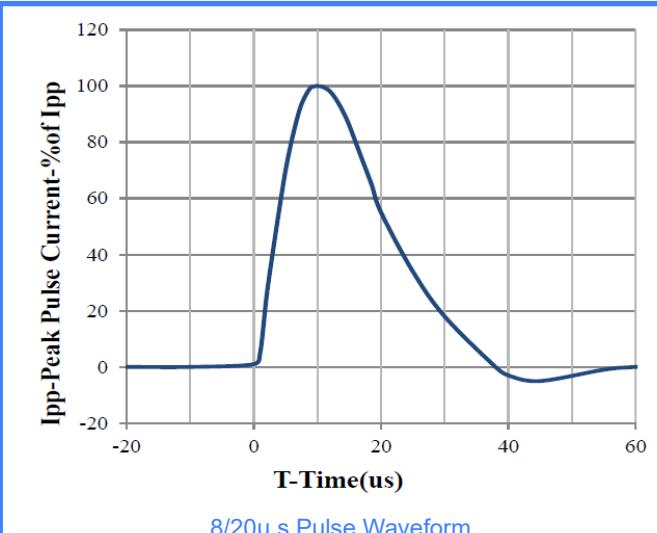
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform

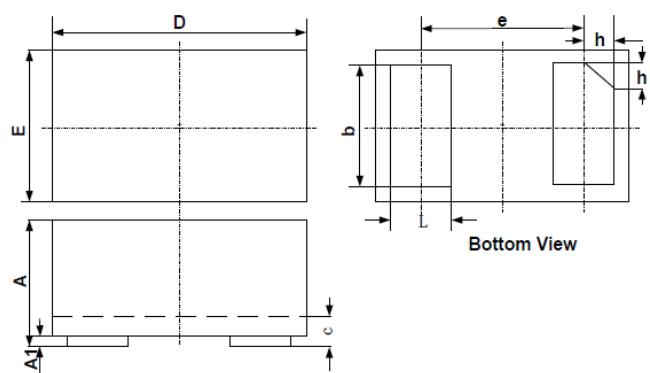


Power Derating Curve



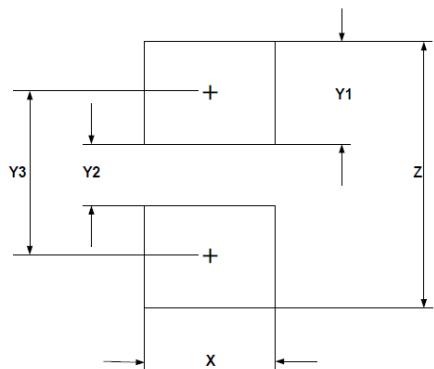
8/20μs Pulse Waveform

DFN1006-2 Package Outline & Dimensions



| SYM | DIMENSIONS | | | | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MILLIMETERS | | | INCHES | | |
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.45 | 0.50 | 0.55 | 0.018 | 0.020 | 0.022 |
| A1 | 0.00 | 0.02 | 0.05 | 0.000 | 0.001 | 0.002 |
| b | 0.45 | 0.50 | 0.55 | 0.018 | 0.020 | 0.022 |
| c | 0.12 | 0.15 | 0.18 | 0.005 | 0.006 | 0.007 |
| D | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| E | 0.55 | 0.60 | 0.65 | 0.022 | 0.024 | 0.026 |
| L | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 |
| L1 | 0.05REF | | | 0.002REF | | |
| h | 0.07 | 0.12 | 0.17 | 0.003 | 0.005 | 0.007 |

Suggested Land Pattern



| SYM | DIMENSIONS | |
|-----|-------------|--------|
| | MILLIMETERS | INCHES |
| X | 0.60 | 0.024 |
| Y1 | 0.50 | 0.020 |
| Y2 | 0.30 | 0.012 |
| Y3 | 0.80 | 0.032 |
| Z | 1.30 | 0.052 |